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(30) Priority:	(71) Applicant: MITSUBISHI ELECTRIC CORP
(43) Date of application publication: 03.08.93	(72) Inventor: SHIMODA HIROSHI
(84) Designated contracting states:	(74) Representative:

**(54) PRODUCTION FOR
SEMICONDUCTOR DEVICE****(57) Abstract:**

PURPOSE: To shorten a working hour which is long time (about 2 hours) in the conventional method, when producing an electrode for semiconductor element.

CONSTITUTION: A plating solution 5 is blown to a wafer 1, on which the semiconductor element is formed, and when current is applied between a cathode electrode 13 opposite to the wafer 1 and a current regulating anode electrode 8 to form the element electrode, high, low and reverse current are applied repeatedly from a current control type D.C. power source 10.

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